

January 1996

### Features

- Devices QML Qualified in Accordance with MIL-PRF-38535
- Detailed Electrical and Screening Requirements are Contained in SMD# 5962-96704 and Intersil's Intersil QM Plan
- 1.25 Micron Radiation Hardened SOS CMOS
- Total Dose ..... >300K RAD (Si)
- Single Event Upset (SEU) Immunity: <math> <1 \times 10^{-10}</math> Errors/Bit/Day (Typ)
- SEU LET Threshold ..... >100 MEV-cm<sup>2</sup>/mg
- Dose Rate Upset ..... >10<sup>11</sup> RAD (Si)/s, 20ns Pulse
- Dose Rate Survivability ..... >10<sup>12</sup> RAD (Si)/s, 20ns Pulse
- Latch-Up Free Under Any Conditions
- Military Temperature Range ..... -55°C to +125°C
- Significant Power Reduction Compared to ALSTTL Logic
- DC Operating Voltage Range ..... 4.5V to 5.5V
- Input Logic Levels
  - VIL = 30% of VCC Max
  - VIH = 70% of VCC Min
- Input Current ≤ 1μA at VOL, VOH
- Fast Propagation Delay ..... 21ns (Max), 14ns (Typ)

### Description

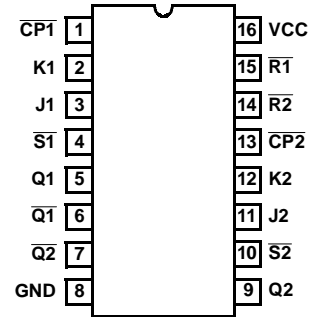
The Intersil ACS112MS is a Radiation Hardened Dual J-K Flip-Flop with Set and Reset. The output change states on the negative transition of the clock (CP1N or CP2N).

The ACS112MS utilizes advanced CMOS/SOS technology to achieve high-speed operation. This device is a member of the radiation hardened, high-speed, CMOS/SOS Logic Family.

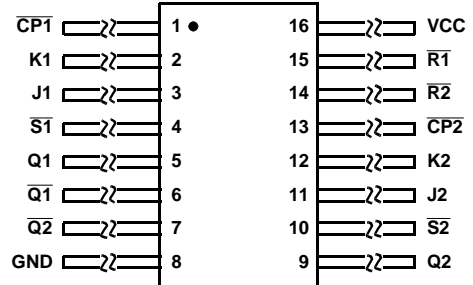
The ACS112MS is supplied in a 16 lead Ceramic Flatpack (K suffix) or a Ceramic Dual-In-Line Package (D suffix).

### Pinouts

16 PIN CERAMIC DUAL-IN-LINE  
MIL-STD-1835, DESIGNATOR CDIP2-T16,  
LEAD FINISH C  
TOP VIEW



16 PIN CERAMIC FLATPACK  
MIL-STD-1835, DESIGNATOR CDFP4-F16,  
LEAD FINISH C  
TOP VIEW

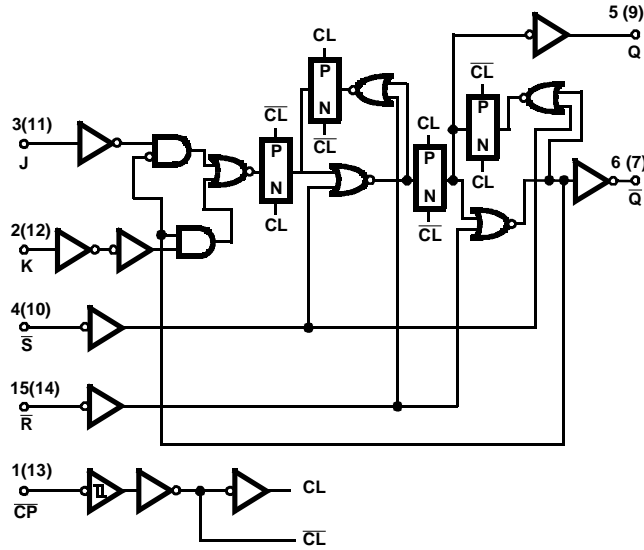


### Ordering Information

PART NUMBER	TEMPERATURE RANGE	SCREENING LEVEL	PACKAGE
5962F9670401VEC	-55°C to +125°C	MIL-PRF-38535 Class V	16 Lead SBDIP
5962F9670401VXC	-55°C to +125°C	MIL-PRF-38535 Class V	16 Lead Ceramic Flatpack
ACS112D/Sample	25°C	Sample	16 Lead SBDIP
ACS112K/Sample	25°C	Sample	16 Lead Ceramic Flatpack
ACS112HMSR	25°C	Die	Die

# ACS112MS

## Functional Diagram



**TRUTH TABLE**

INPUTS					OUTPUTS	
$\bar{S}$	$\bar{R}$	$\bar{CP}$	J	K	Q	$\bar{Q}$
L	H	X	X	X	H	L
H	L	X	X	X	L	H
L	L	X	X	X	H (Note 2)	H (Note 2)
H	H		L	L	No Change	
H	H		H	L	H	L
H	H		L	H	L	H
H	H		H	H	Toggle	
H	H	H	X	X	No Change	

**NOTES:**

1. H = High Steady State, L = Low Steady State, X = Immaterial, = High-to-Low Transition
2. Output States Unpredictable if  $\bar{S}$  and  $\bar{R}$  Go High Simultaneously after Both being Low at the Same Time

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# ACS112MS

## Die Characteristics

### DIE DIMENSIONS:

88 mils x 88 mils  
2.24mm x 2.24mm

### METALLIZATION:

Type: AlSi  
Metal 1 Thickness:  $7.125\text{k}\text{\AA} \pm 1.125\text{k}\text{\AA}$   
Metal 2 Thickness:  $9\text{k}\text{\AA} \pm 1\text{k}\text{\AA}$

### GLASSIVATION:

Type:  $\text{SiO}_2$   
Thickness:  $8\text{k}\text{\AA} \pm 1\text{k}\text{\AA}$

### WORST CASE CURRENT DENSITY:

$< 2.0 \times 10^5 \text{A/cm}^2$

### BOND PAD SIZE:

$110\mu\text{m} \times 110\mu\text{m}$   
4.3 mils x 4.3 mils

## Metallization Mask Layout

